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Watanabe, H.; Tatsumi, T.; Ohnishi, S.; Kitajima, H.; Honma, I.; Ikarashi, T.; H.;

Electron Devices, IEEE Transactions on , Volume: 42 , Issue: 7 , July 1995  
Pages:1247 - 1254[\[Abstract\]](#) [\[PDF Full-Text \(600 KB\)\]](#) **IEEE JNL****2 Raman spectroscopy, high pressure phosphine anneal, and the elect properties of the DRAM capacitor**

Sawaya, S.;

Advanced Semiconductor Manufacturing Conference, 2001 IEEE/SEMI , 23-24 2001

Pages:95

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